

RF2P-HS-TS22ULL

Dual Port (1 read only port, 1 write only port)

Register File Compiler

Ultra-Low Leakage: High V_T (HV_T) are used to minimize leakage performance.

Bit Cell: Utilizes Foundries 8T bit cells to ensure high manufacturing yields

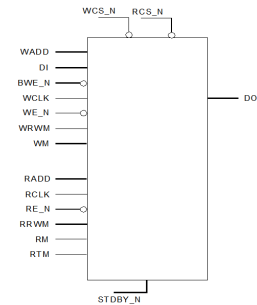
Deep Sleep Mode Retains data a minimal power consumption. Dedicated standby mode reduces power required to an absolute minimum to retain the memory contents.

Isolated Array and Periphery supplies: Periphery voltage can be shut off to further reduce standby power. Both periphery and array can be supplied with the same .9 V Supply

Adjustable Internal Read and Write Timing Margins

BIST Muxes can optionally be added to the wrapper

Bit Write Enable: Allows independent write operations to any subset of a memory word.



Technology	22ULL	Max Instance	36 Kbits	EDA Views (Partial List)	
Voltage	0.9V (0.81V to 0.99V)	Min Instance	128 Bits	Verilog Model with UPF	
Temperature	-40°C to +125°C	Word Width	8 – 78	Liberty Files (NLDM, LVF, CCS)	
Power	Mesh	Word Depth	16 - 512	PDF and Text Datasheets	Redhawk APL
# Metal Layers	4	Aspect Ratio	Column Fold: 4	LEF 5.8	Verilog Test Bench
BIST Mux	Internal	User Interface	Command Line	LVS SPICE Netlist	Bitmap File (x, y)
Modes	Functional, BIST, Scan, Sleep	Bit Write Enable	Optional	GDS	Power Grid (Volutus)
				Tessent MBIST Control File	Common Power Format (CPF)

About Mobile Semiconductor:

Nordic Semiconductor’s Seattle, Washington memory team continues building on the technology acquired from Mobile Semiconductor. SRAM, ROM, and Register File compilers are available for applications requiring ultra-low power, low leakage, or ultra-high performance.

<http://www.mobile-semiconductor.com/>

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